IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Kangguo CHENG, et. al.

Group Art Unit: Unknown

Serial No.: Not assigned yet

Examiner: unknown

Filed: Concurrently herewith

For: STRAINED SILICON ON A SIGE ON SOI SUBSTRATE

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. 1.56

Sir:

Under provisions of 37 C.F.R. 1.97 through 1.99 and pursuant to applicant's duty of disclosure under 37 C.F.R. 1.56, applicants respectfully bring the documents listed on the attached Form PTO-1449 to the attention of the Examiner in charge of the above-identified application. A copy of the non-US patent documents is enclosed for the convenience of the Examiner.

This citation does not constitute an admission that the cited references are relevant or material to the claims nor should it be construed as a representation that no other art than that identified exists. They are merely cited as constituting related art of which the applicant is aware.

It is respectfully requested that these documents be considered by the Examiner and formally made of record in this application.

Respectfully submitted,

Andrew M. Calderon

Reg. No. 38,093

McGuireWoods LLP 1750 Tysons Boulevard, Suite 1800 McLean, VA 22102 (703)712-5000

FORM PTO-	144	49 (Modified)		ATTY. DOCKET NO. FIS9-2003-0240		SERIAL NO. Unassigned	-				
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EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS SUBCLA		FILING DATES (IF APPRO				
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation is not in conformance and not considered. Include copy of this form with next communication to applicant.

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